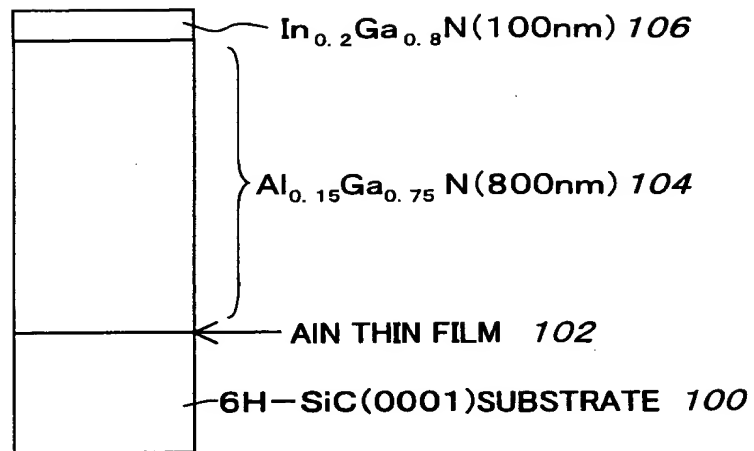


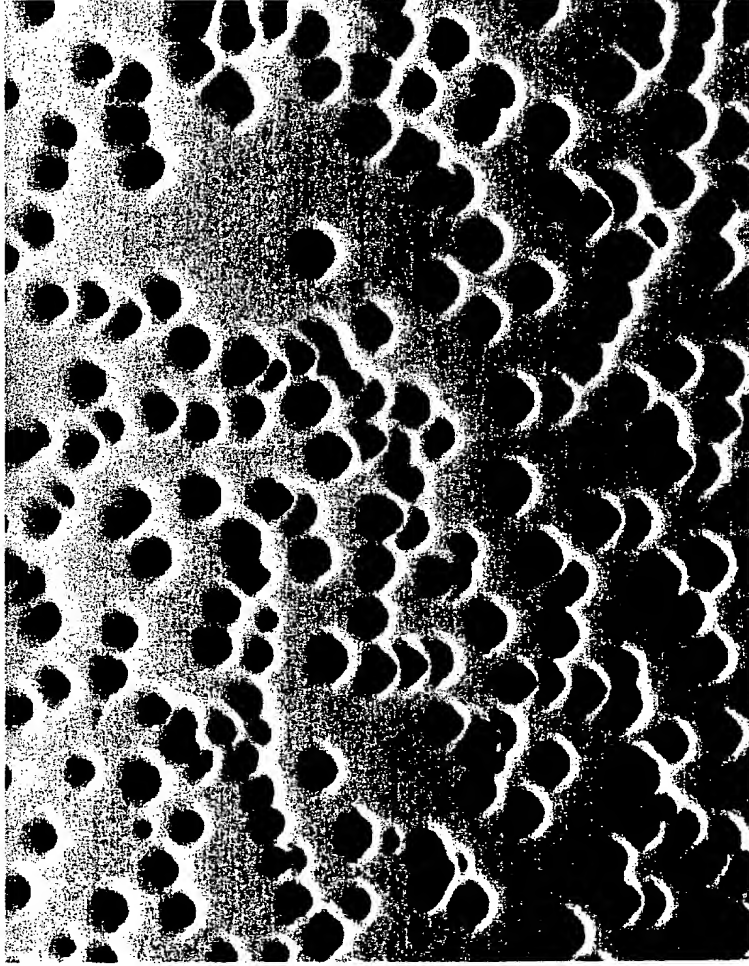
*FIG. 1*



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T01E80" 222E4660

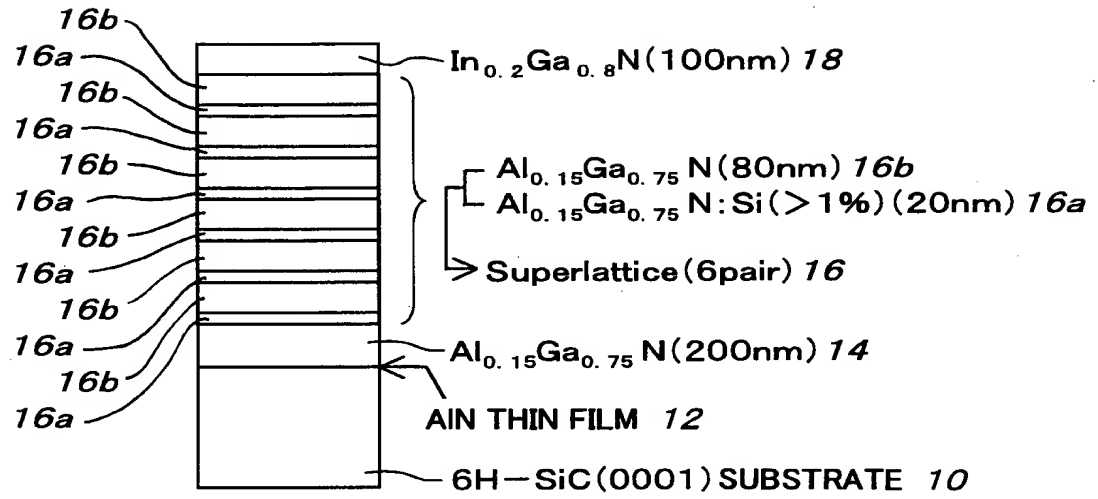
FOIEBO" 222E4660

*FIG. 2*



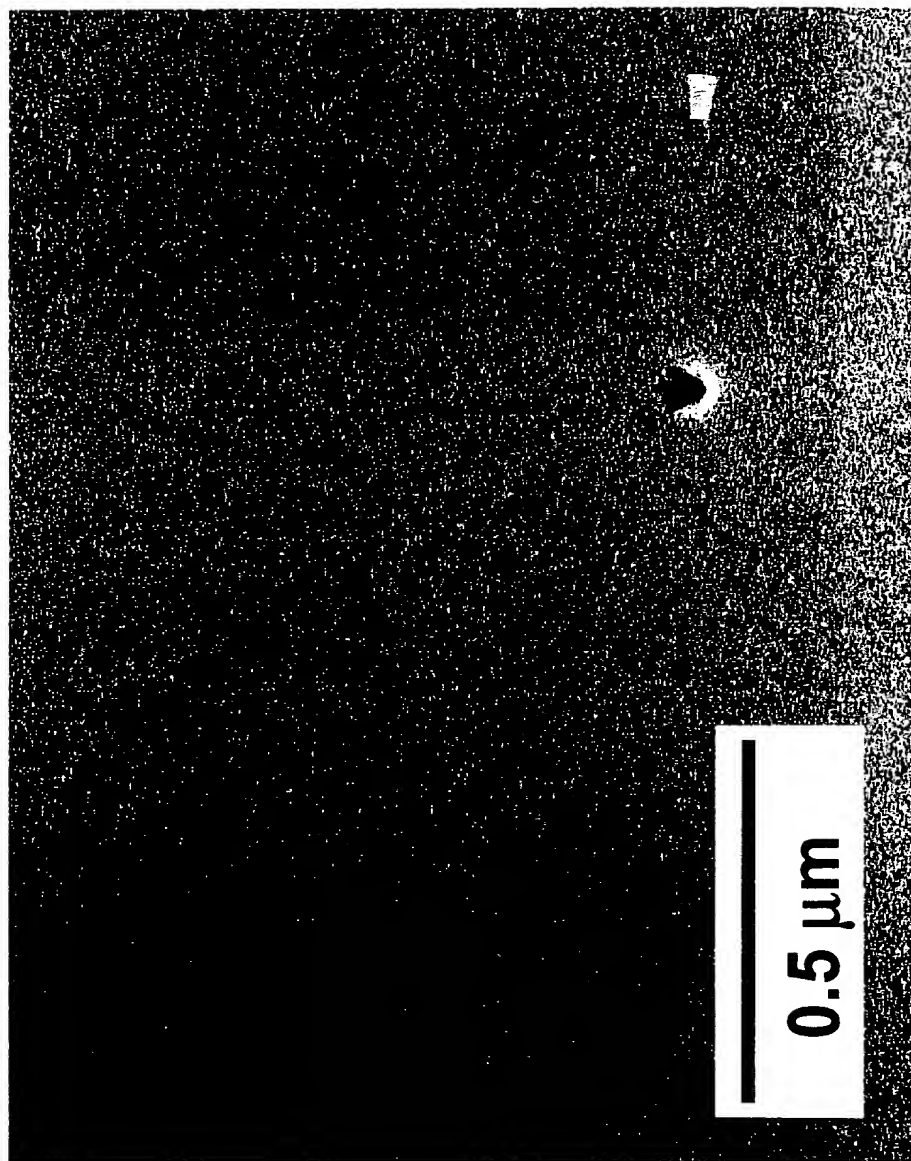
0.5  $\mu\text{m}$

# FIG. 3

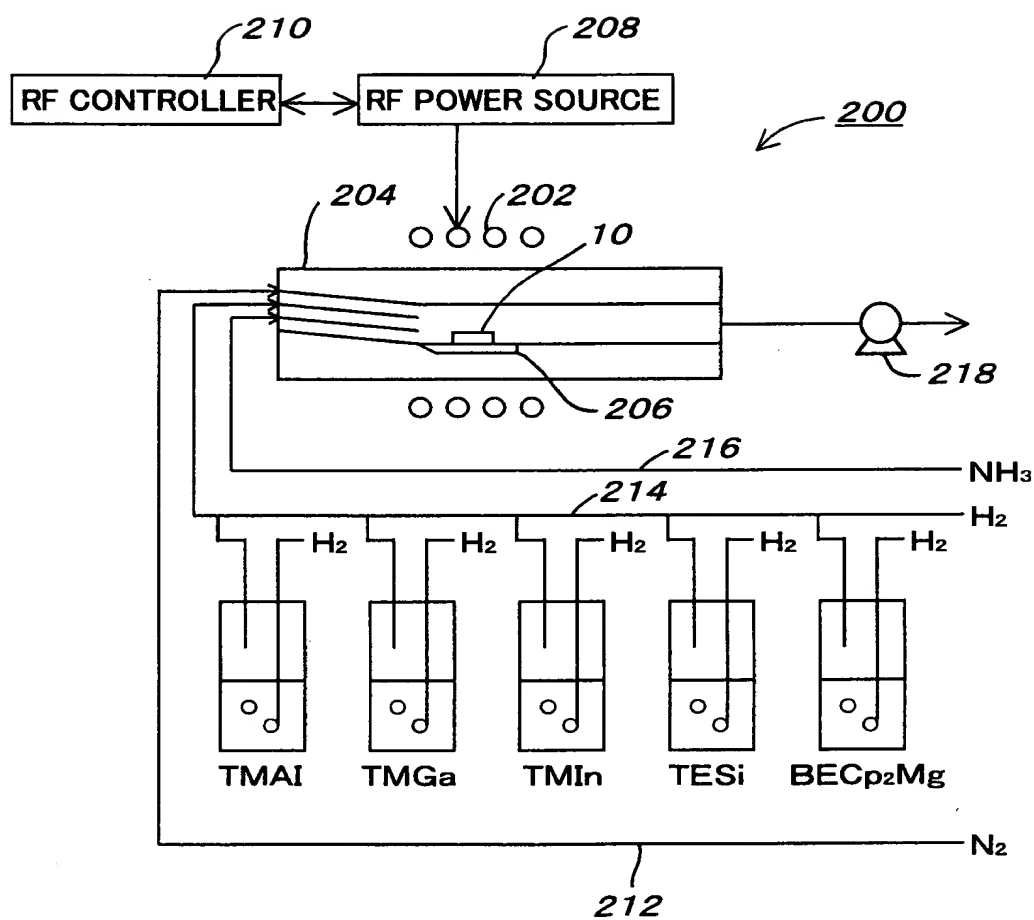


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*FIG. 4*



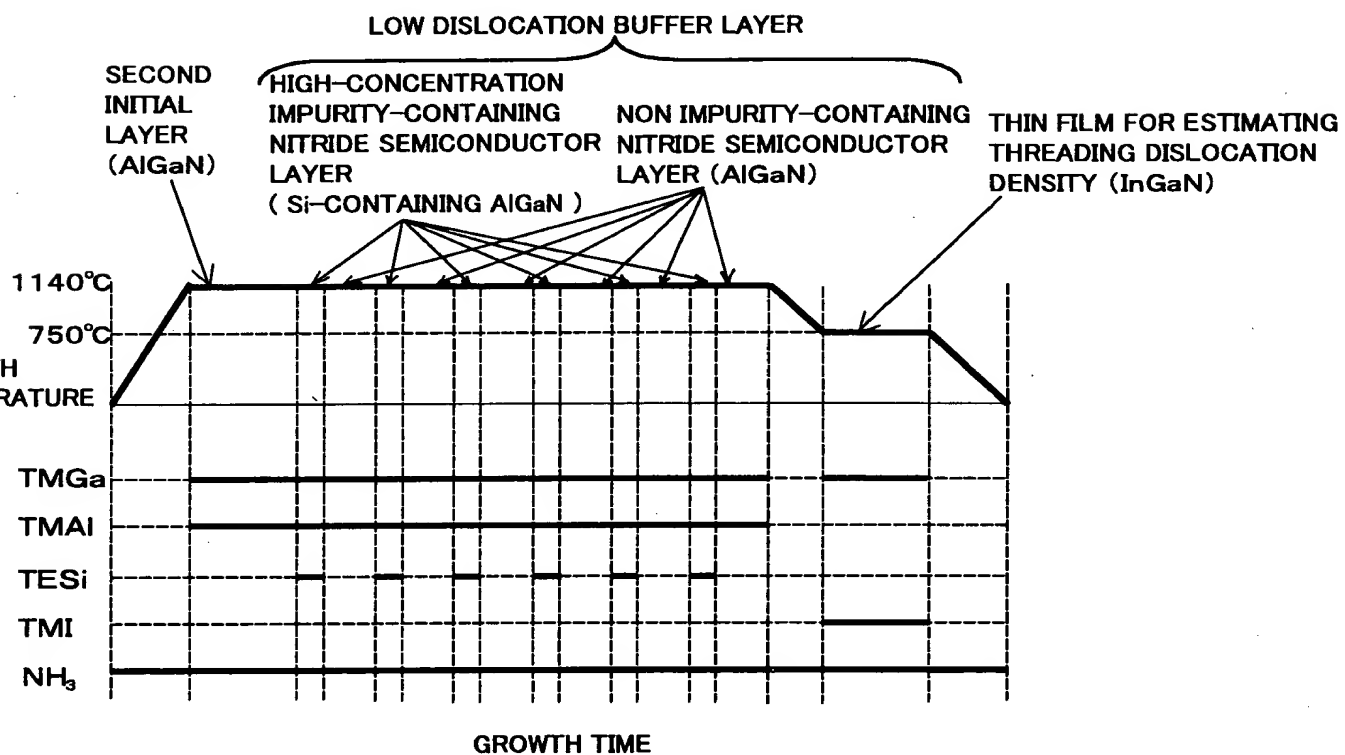
# FIG. 5



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# FIG. 6

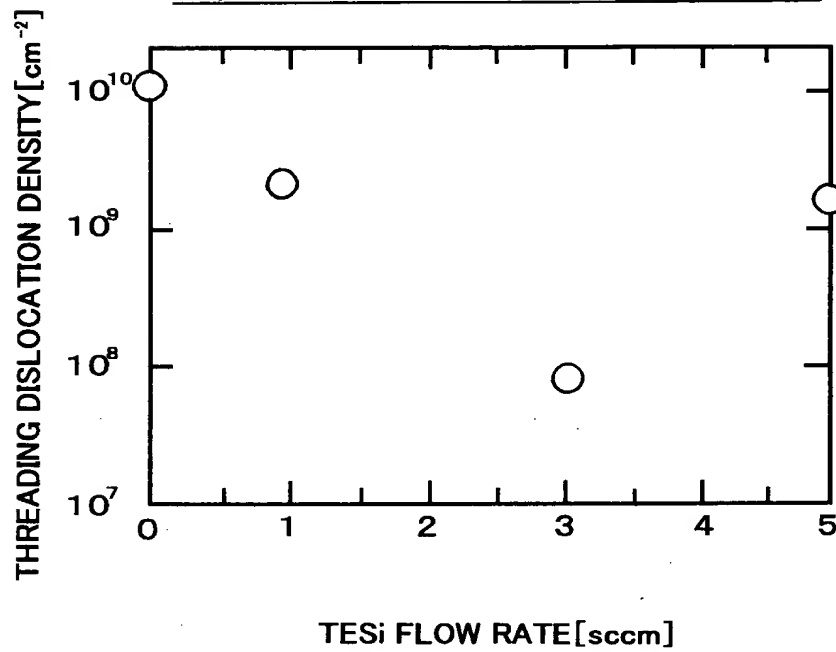
## TIMING CHART FOR INTRODUCING MATERIAL GASES



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# FIG. 7

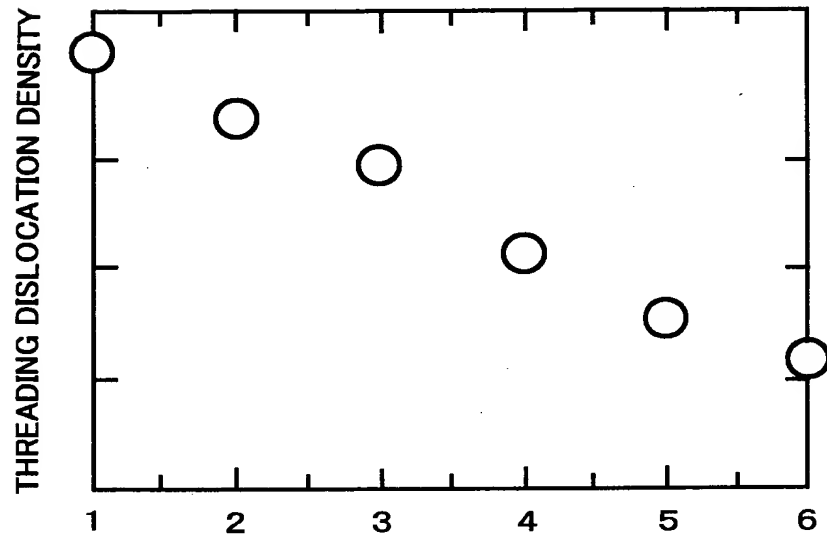
RELATIONSHIP BETWEEN TESi FLOW RATE  
AND THREADING DISLOCATION DENSITY



101E30"22E4660

# FIG. 8

RELATIONSHIP BETWEEN PERIOD OF  
SUPERLATTICE BUFFER LAYER AND  
THREADING DISLOCATION DENSITY



PERIODICITY OF SUPERLATTICE BUFFER LAYER (NUMBER OF TIMES)



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FIG. 9

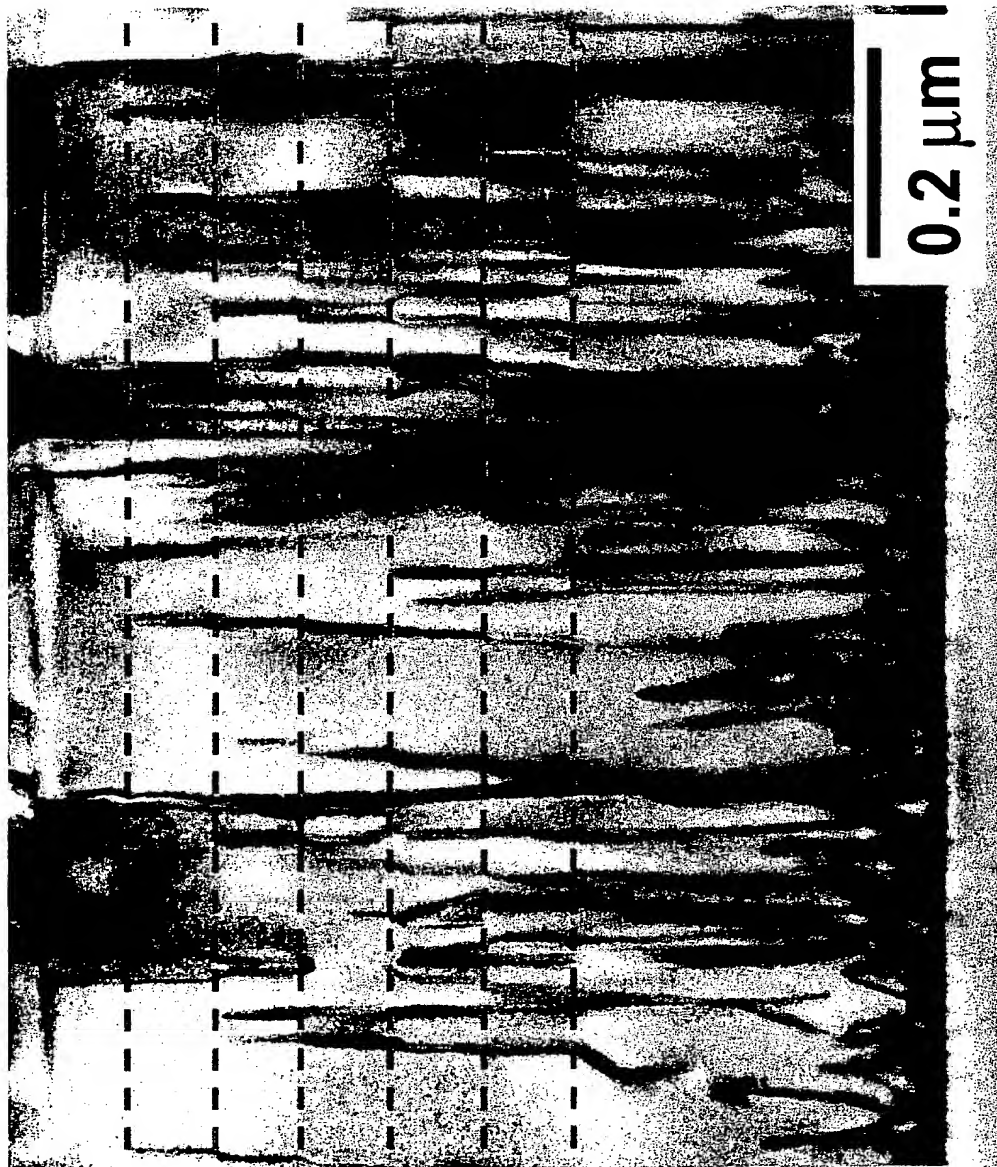
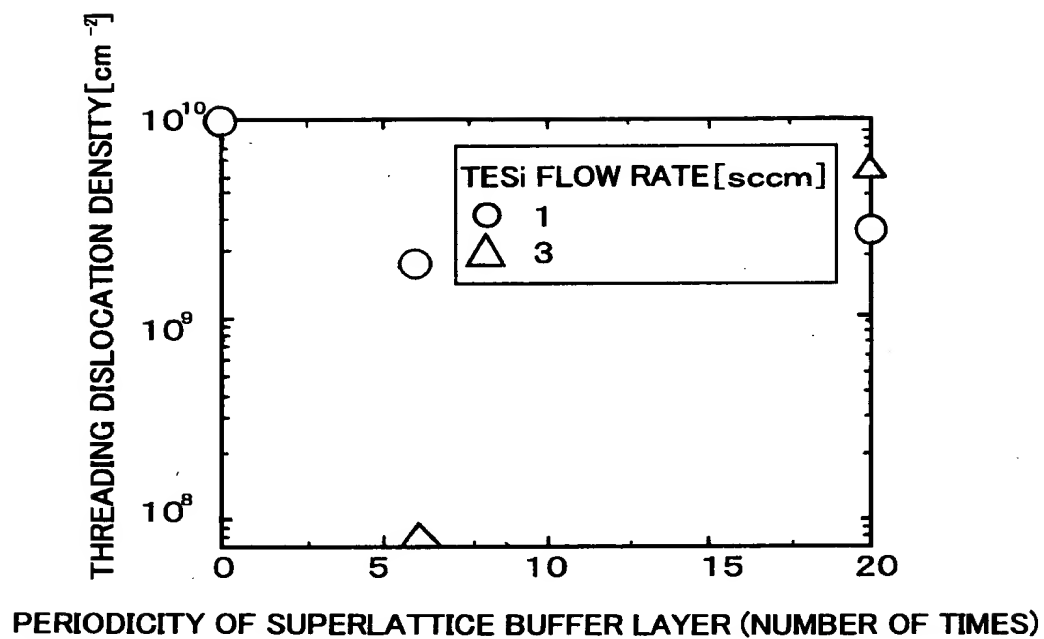


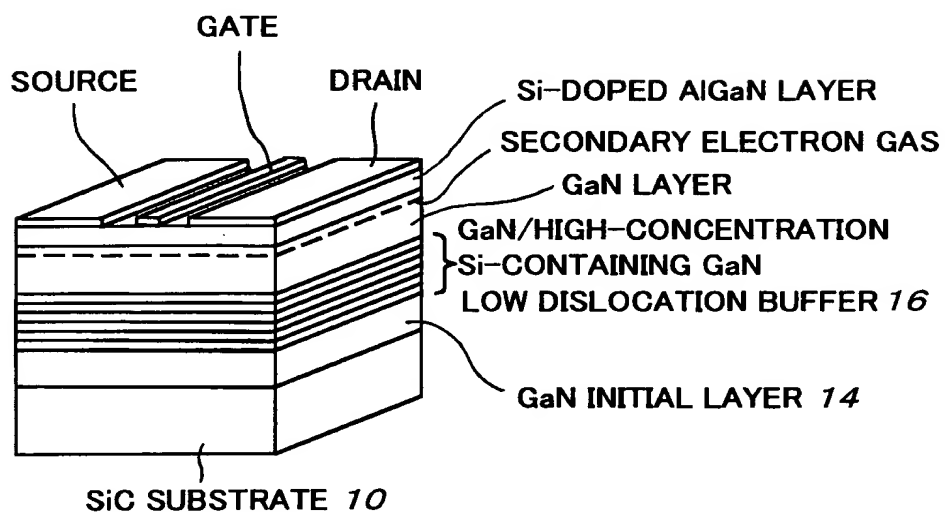
FIG. 10



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# FIG. 11

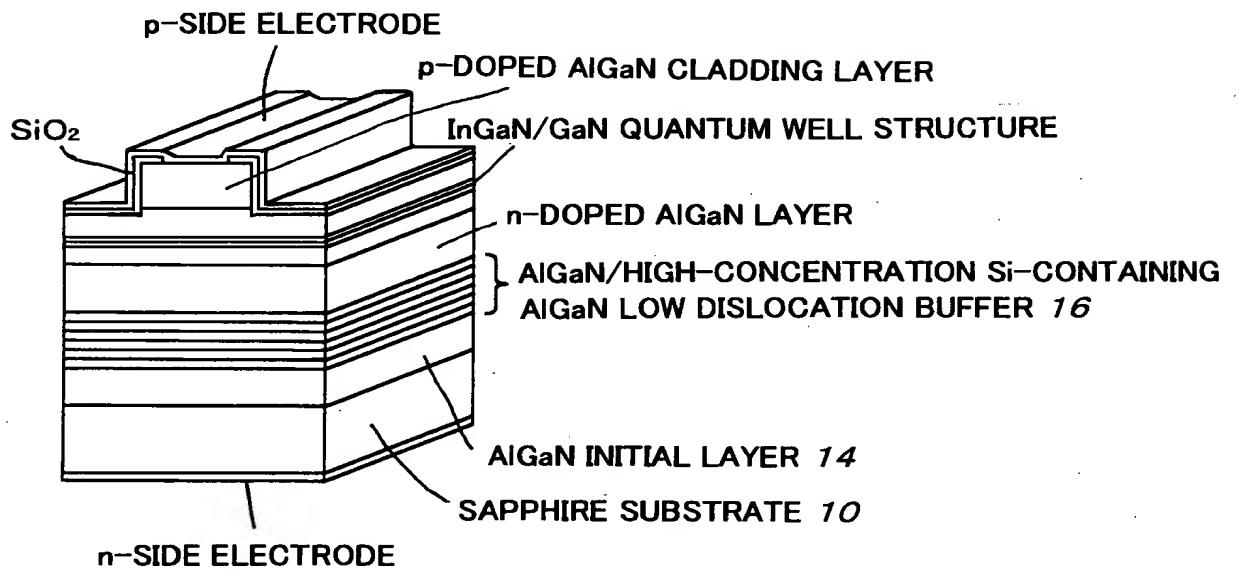
NITRIDE SEMICONDUCTOR HFET  
(Heterostructure Field Effect Transistor)  
(EXAMPLE, AlGaN/GaN-HFET)



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# FIG. 12

NITRIDE SEMICONDUCTOR LASER DIODE  
(EXAMPLE, InGaN LASER)



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